

**/ Descriptions**

TO-262          N      MOS          N-CHANNEL MOSFET in a TO-262 Plastic Package..

**/ Features**

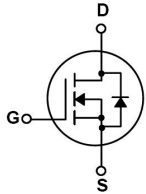
Low gate charge, low crss, fast switching.

**/ Applications**

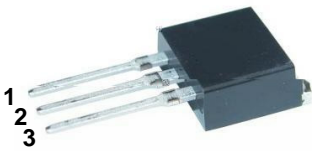
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

**/ Equivalent Circuit**



**/ Pinning**



PIN1 G          PIN 2 D          PIN 3 S

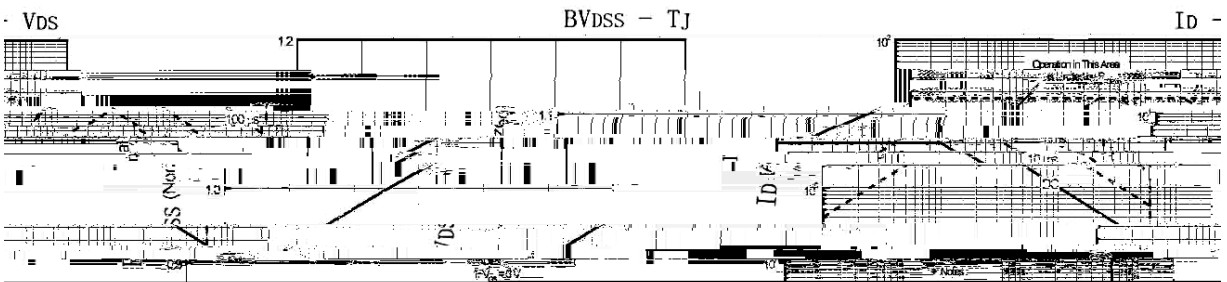
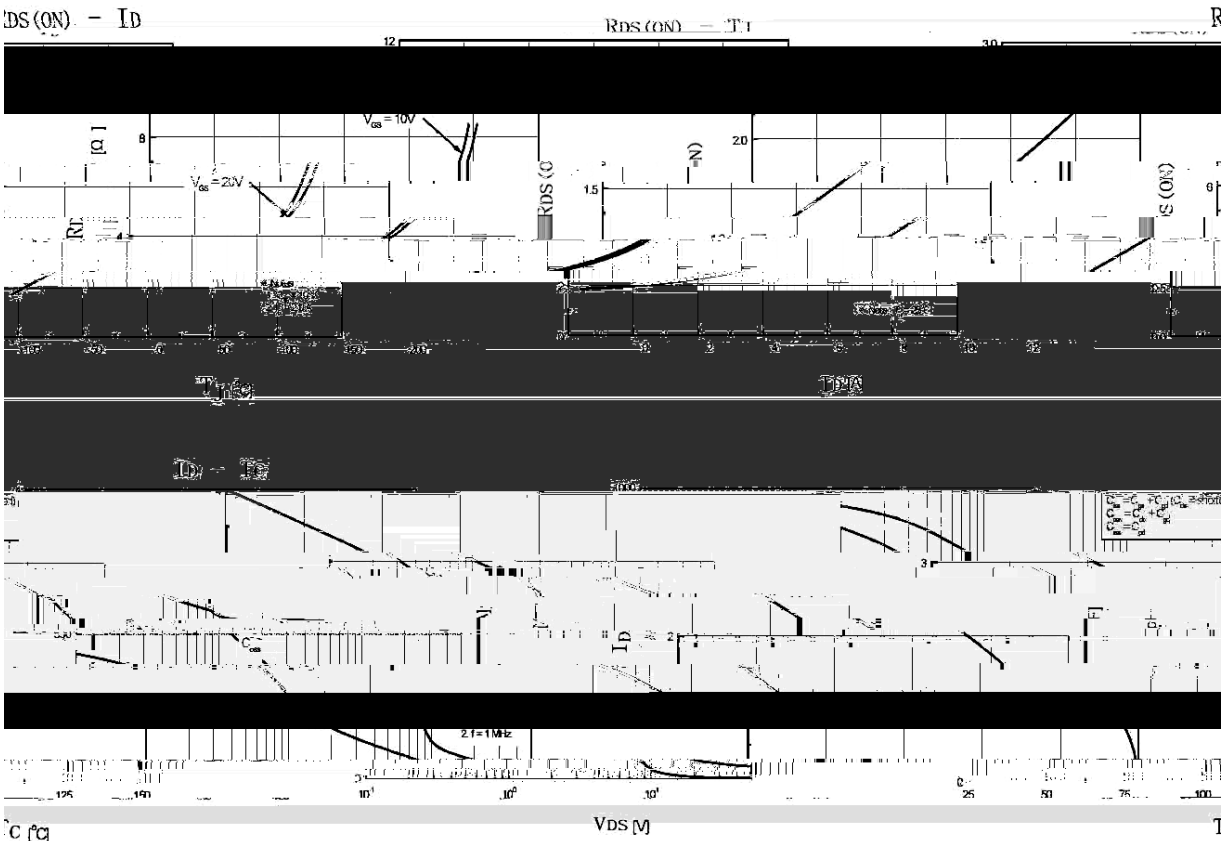
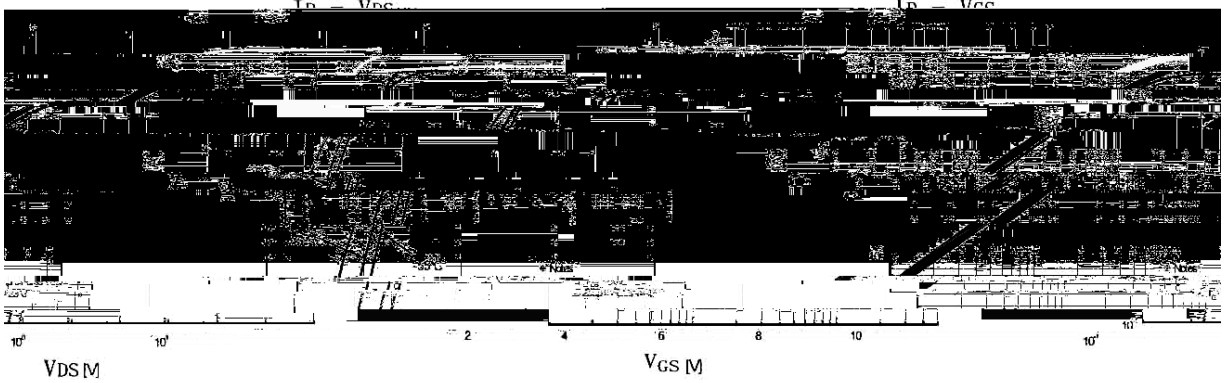
**/ h<sub>FE</sub> Classifications & Marking**

See Marking Instructions.

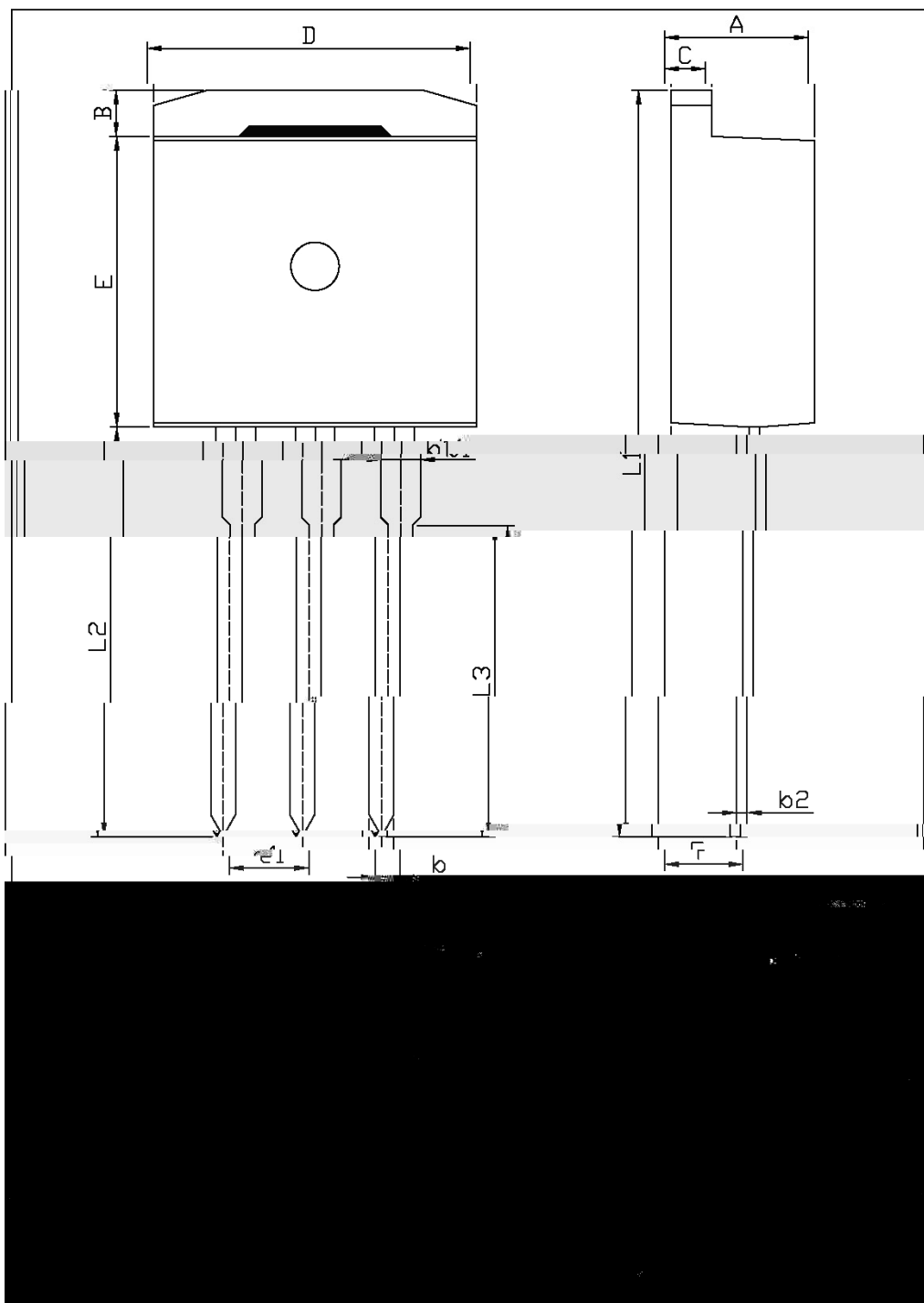
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DSS}$	600	V
Drain Current	$I_D(T_C=25^\circ\text{C})$	4.0	A
Drain Current	$I_D(T_C=100^\circ\text{C})$	2.5	A
Drain Current - Pulsed	$I_{DM}$	16	A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Single Pulsed Avalanche Energy	$E_{AS}$	240	mJ
Repetitive Avalanche Energy	$E_{AR}$	10	mJ
Avalanche Current	$I_{AR}$	4.0	A
Power Dissipation	$P_D(T_C=25^\circ\text{C})$	100	W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V$ $I_D=250\mu A$	600			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=600V$ $V_{GS}=0V$			10	$\mu A$
		$V_{DS}=480V$ $T_C=125^\circ\text{C}$			100	$\mu A$
Gate-Body Leakage Current Forward	$I_{GSS}$	$V_{GS}=\pm 30V$ $V_{DS}=0V$			$\pm 0.1$	

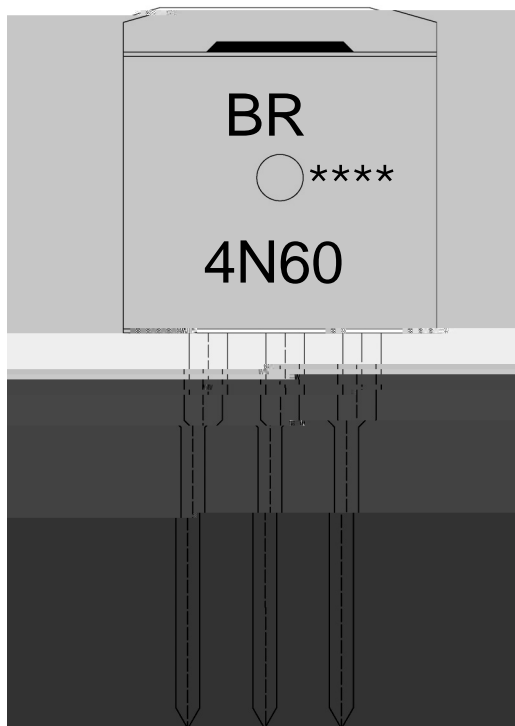
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

4N60

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Note:

BR: Company Code

4N60: Product Type.

\*\*\*\*: Lot No. Code, code change with Lot No.

